

## Thyristor/Diode Modules

**V<sub>RRM</sub> / V<sub>DRM</sub>** 800 to 1600V  
**I<sub>TAV</sub>** 60Amp

### Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control

### Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DCB ceramic isolated metal baseplate

### Module Type

TYPE	V <sub>RRM</sub>	V <sub>RSM</sub>
MSTC60-08	800V	900V
MSTC60-12	1200V	1300V
MSTC60-16	1600V	1700V

### Maximum Ratings

Symbol	Conditions	Values	Units
I <sub>TAV</sub>	Sine 180°; T <sub>c</sub> =85°C	60	A
I <sub>TSM</sub>	T <sub>VJ</sub> =45°C t=10ms, sine T <sub>VJ</sub> =125°C t=10ms, sine	1500 1250	A
i <sup>2</sup> t	T <sub>VJ</sub> =45°C t=10ms, sine T <sub>VJ</sub> =125°C t=10ms, sine	11000 8000	A2s
Visol	a.c.50HZ;r.m.s.;1min	3000	V
T <sub>VJ</sub>		-40 to 125	°C
T <sub>Stg</sub>		-40 to 125	°C
M <sub>t</sub>	To terminals(M5)	3±15%	Nm
M <sub>s</sub>	To heatsink(M6)	5±15%	Nm
di/dt	T <sub>VJM</sub> = T <sub>VJM</sub> , 2/3V <sub>DRM</sub> , I <sub>G</sub> =500mA Tr<0.5us, tp>6us	150	A/us
dv/dt	T <sub>VJM</sub> = T <sub>VJM</sub> , 2/3V <sub>DRM</sub> , linear voltage rise	1000	V/us
a	Maximum allowable acceleration	50	m/s <sup>2</sup>
Weight	Module(Approximately)	100	g

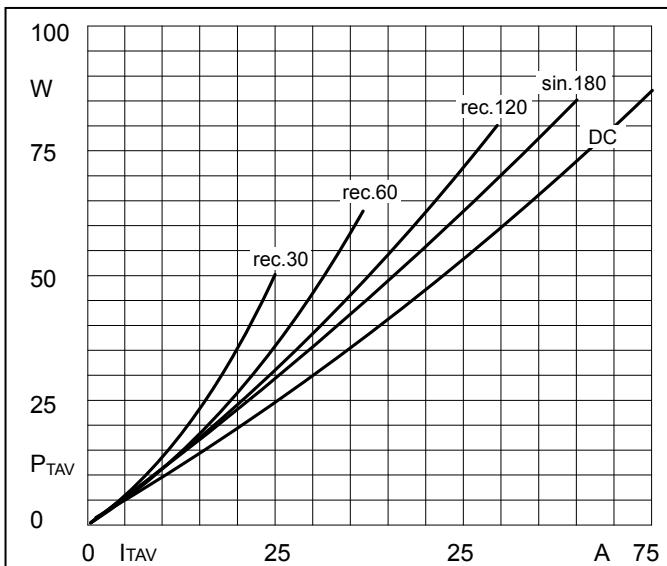
### Thermal Characteristics

Symbol	Conditions	Values	Units
R <sub>th(j-c)</sub>	Cont.;per thyristor / per module	0.57/0.29	°C/W
R <sub>th(c-s)</sub>	per thyristor / per module	0.2/0.1	°C/W

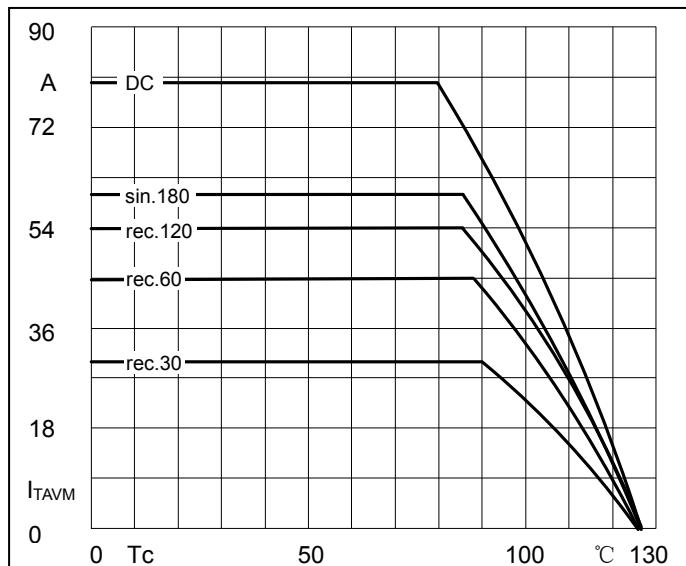
## Electrical Characteristics

Symbol	Conditions	Values			Units
		Min.	Typ.	Max.	
$V_{TM}$	$T=25^\circ C$ $I_{TM}=200A$			1.65	V
$I_{RRM}/I_{DRM}$	$T_{VJ}=T_{VJM}$ , $V_R=V_{RRM}$ , $V_D=V_{DRM}$			15	mA
$V_{TO}$	For power-loss calculations only ( $T_{VJ}=125^\circ C$ )			0.9	V
$r_T$	$T_{VJ}=T_{VJM}$			3.5	$m\Omega$
$V_{GT}$	$T_{VJ}=25^\circ C$ , $V_D=6V$			3.0	V
$I_{GT}$	$T_{VJ}=25^\circ C$ , $V_D=6V$			150	mA
$V_{GD}$	$T_{VJ}=125^\circ C$ , $V_D=2/3V_{DRM}$			0.25	V
$I_{GD}$	$T_{VJ}=125^\circ C$ , $V_D=2/3V_{DRM}$			6	mA
$I_L$	$T_{VJ}=25^\circ C$ , $R_G=33 \Omega$	300	600		mA
$I_H$	$T_{VJ}=25^\circ C$ , $V_D=6V$	150	250		mA
tgd	$T_{VJ}=25^\circ C$ , $I_G=1A$ , $dI_G/dt=1A/\mu s$	1			$\mu s$
tq	$T_{VJ}=T_{VJM}$	80			$\mu s$

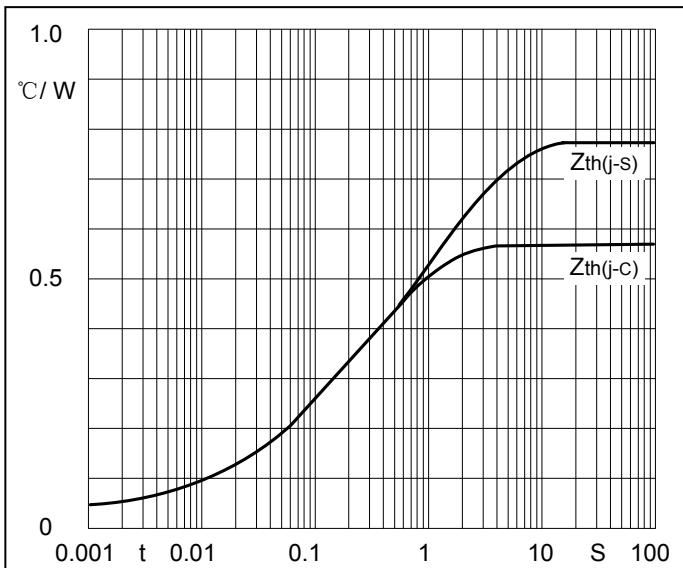
## Performance Curves



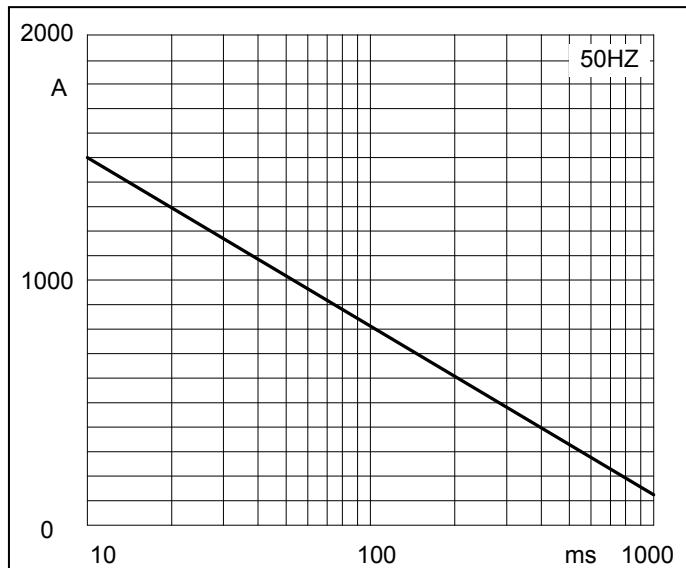
**Fig1. Power dissipation**



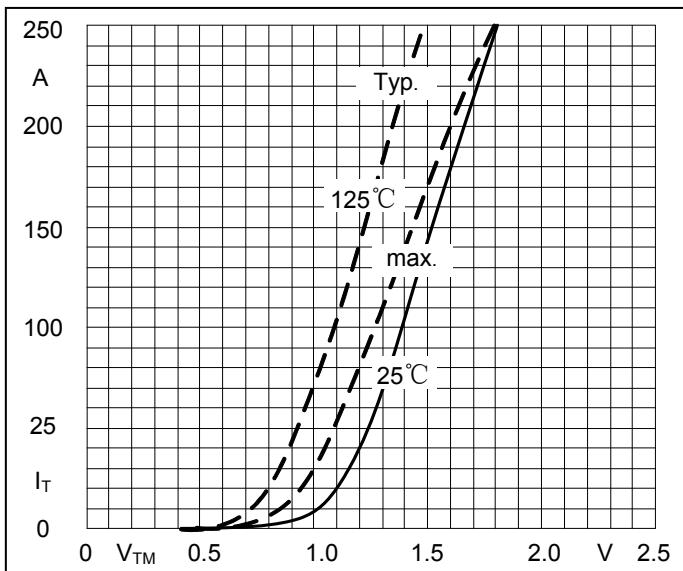
**Fig2. Forward Current Derating Curve**



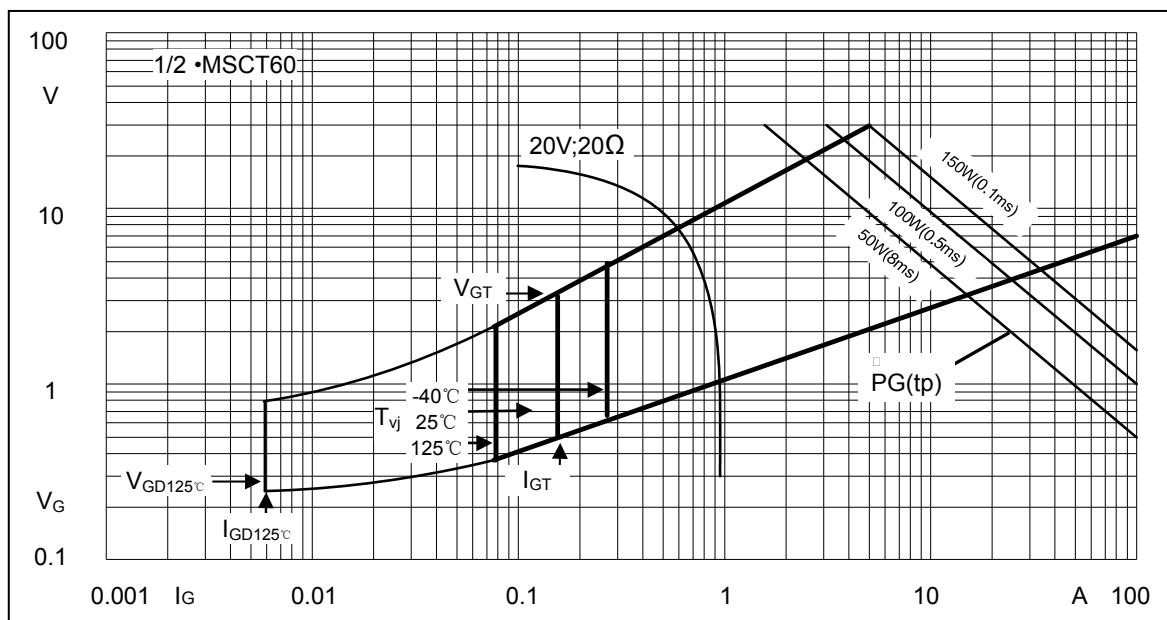
**Fig3. Transient thermal impedance**



**Fig4. Max Non-Repetitive Forward Surge Current**



**Fig5. Forward Characteristics**



**Fig6. Gate trigger Characteristics**

### Package Outline Information

